Supplementary Materials for
Ambipolar Transport in Narrow Bandgap Semiconductor InSb Nanowires

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In the main article, we showed the measured ambipolar transport characteristics of an InSb NWFET with a channel length of 1 μm at source-drain bias voltage V_D=100 mV and of an InSb NWFET with a channel length of 260 nm at V_D=50 mV at different temperatures. Here, we provide in Figure S1 the measurements for the two devices at several lower source-drain bias voltages at a low temperature of T=4 K. Excellent ambipolar transport characteristics with three distinct transport regions as defined in Figure 2(d) of the main article can be clearly observed in all these measurements.

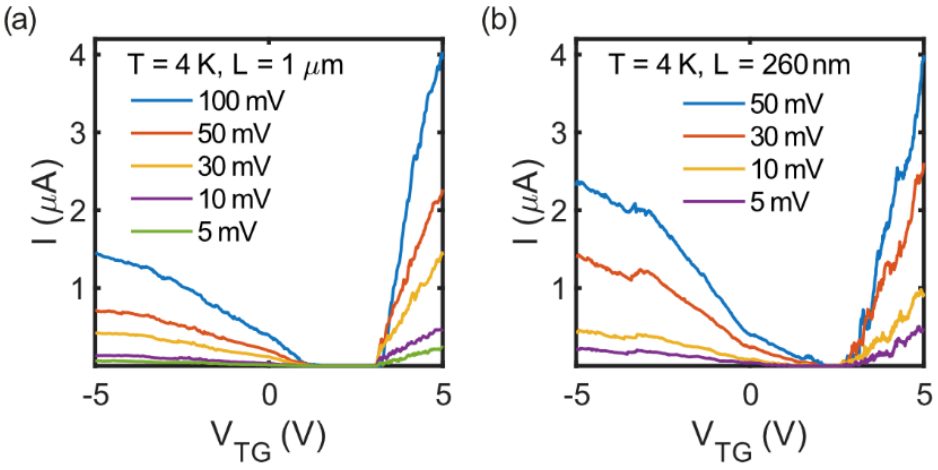

Figure S1. (a) Current I measured as a function of top-gate voltage V_{TG} for the InSb NWFET with a channel length of L= 1 μm at different source-drain bias voltages and at a temperature of T = 4 K. (b) the same as (a) but for the InSb NWFET with a channel length of L = 260 nm. Clear ambipolar transport characteristics can be seen in the measurements of the two devices at all the considered source-drain bias voltages.